

Data Sheet

AL 995TM (Mac-A995W)

Description

High purity alumina ceramic of 99.5% Al₂O₃ content.

Its purity, chemical resistance and high temperature capabilities prove invaluable for semiconductor processing applications.

Prime Features:

- Electrically and dimensionally stable at high temperatures
- Low particle generation
- Dense, non-porous and vacuum tight
- Excellent dielectric properties
- Accepts moly-manganese metallizing for high temperature brazing of vacuum tight assemblies
- Excellent chemical and abrasion resistance

Typical Applications:

- Wafer processing and handling devices
- Components for semiconductor process chambers, spluttering targets, fixtures, etc
- Laser devices for wide range of industrial, medical and defence duties
- Power tubes for klystron and x-ray equipment
- Flow meters and pressure sensors

Specifications

- Quality Assurance to ISO 9001: 2008

Production Capabilities:

- Isostatic and dry pressing, green machining
- CNC grinding and lapping to very tight tolerances
- Metallising of components
- High temperature brazing of assemblies
- Prototype, batch and volume production

Physical Properties

| | | | | |
|--|-------------------------------------|-----------------------------|----------------------|---------------------|
| Colour | White | | | |
| Bulk Density (fired) | 3.86 g/cm ³ | 0.139 lb/in ³ | | |
| Porosity (apparent) | 0 (fully dense) % nominal | | | |
| Rockwell Hardness (R30N) | 81 | | | |
| Compressive Strengths | 2070 MPa | >300,000 lb/in ² | | |
| Flexural Strength | 310 MPa | 45,000 lb/in ² | | |
| Thermal Conductivity | 29.3 W/m.K | 16.9 BTU/ft.hr.°F | | |
| Thermal Expansion Coefficient 10 ⁻⁶ /°C [10 ⁻⁶ /°F] | 25-200°C [77-390°F] | 6.9 [3.8] | | |
| | 200-400°C [390-750°F] | 7.8 [4.3] | | |
| | 400-600°C [750-1110°F] | 8.3 [4.6] | | |
| | 600-800°C [1110-1470°F] | 9.0 [5.0] | | |
| | 800-1000°C [1470-1830°F] | 9.4 [5.2] | | |
| Maximum no-load temperature | 1725°C | 3150 °F | | |
| Dielectric Strength | 31.5 DC kV/mm | 800 V/mil | | |
| Dielectric Constant K' ¹ | 25°C | 300°C | 500°C | |
| | @10MHz | 9.58 | 9.92 | 10.20 |
| | @1000MHz | 9.30 | - | - |
| | @8500MHz | 9.37 | 9.61 | 9.82 |
| Dissipation factor, tanδ | @10MHz | 0.00003 | 0.00009 | 0.00040 |
| | @1000MHz | 0.00014 | - | - |
| | @8500MHz | 0.00009 | 0.00014 | 0.00025 |
| | Loss factor, K' ¹ .tan δ | @10MHz | 0.00029 | 0.00089 |
| @1000MHz | | 0.00130 | - | - |
| @8500MHz | | 0.00084 | 0.00135 | 0.00245 |
| Volume resistivity, ohm.cm: | | > 10 ¹⁴ | 2.0x10 ¹¹ | 2.2x10 ⁹ |